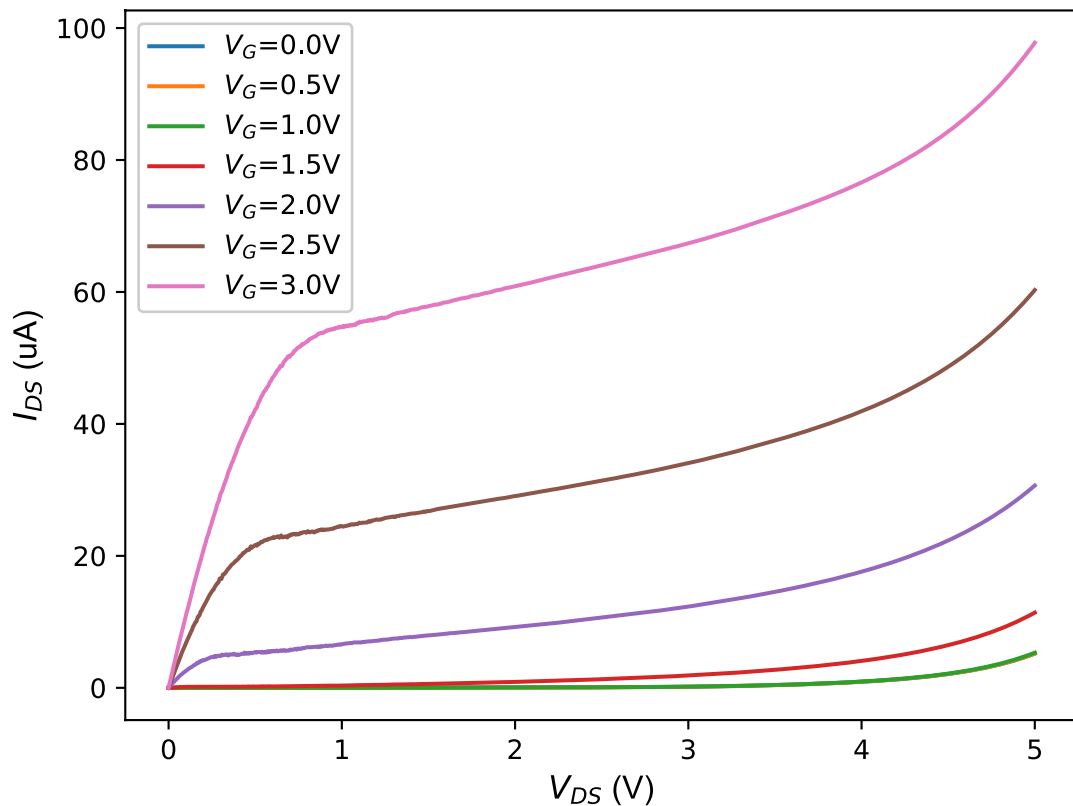
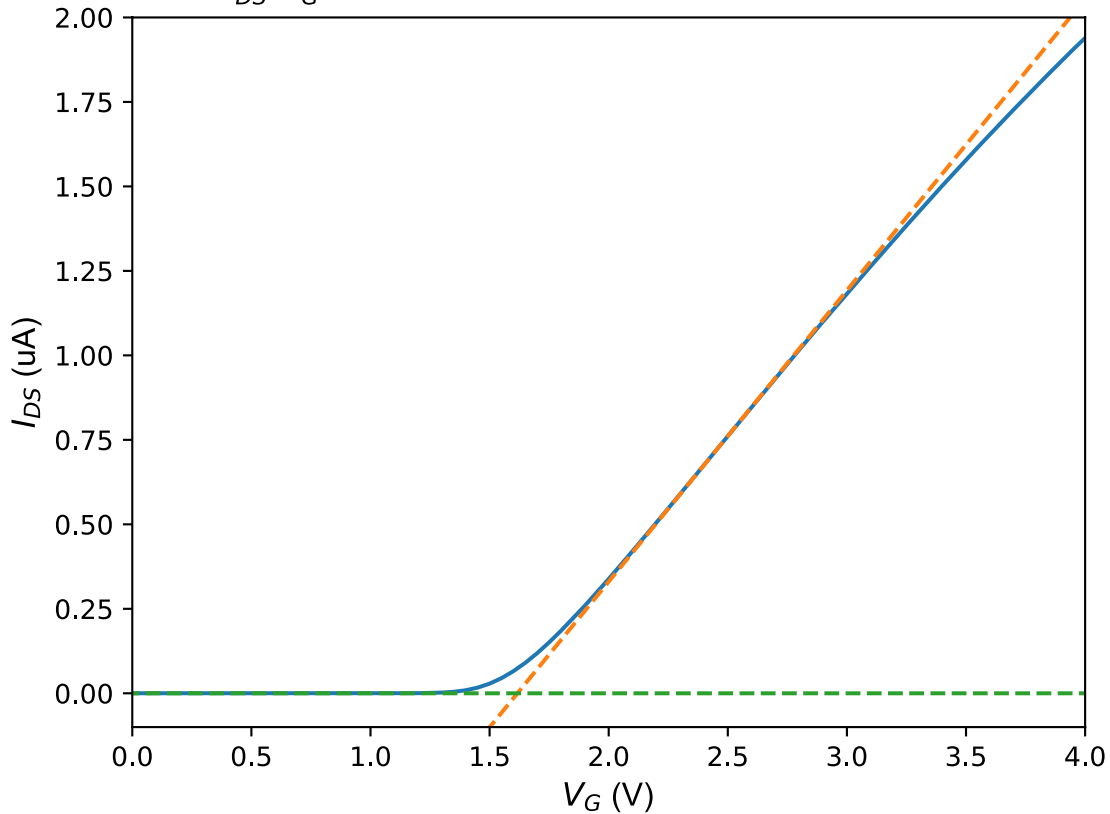


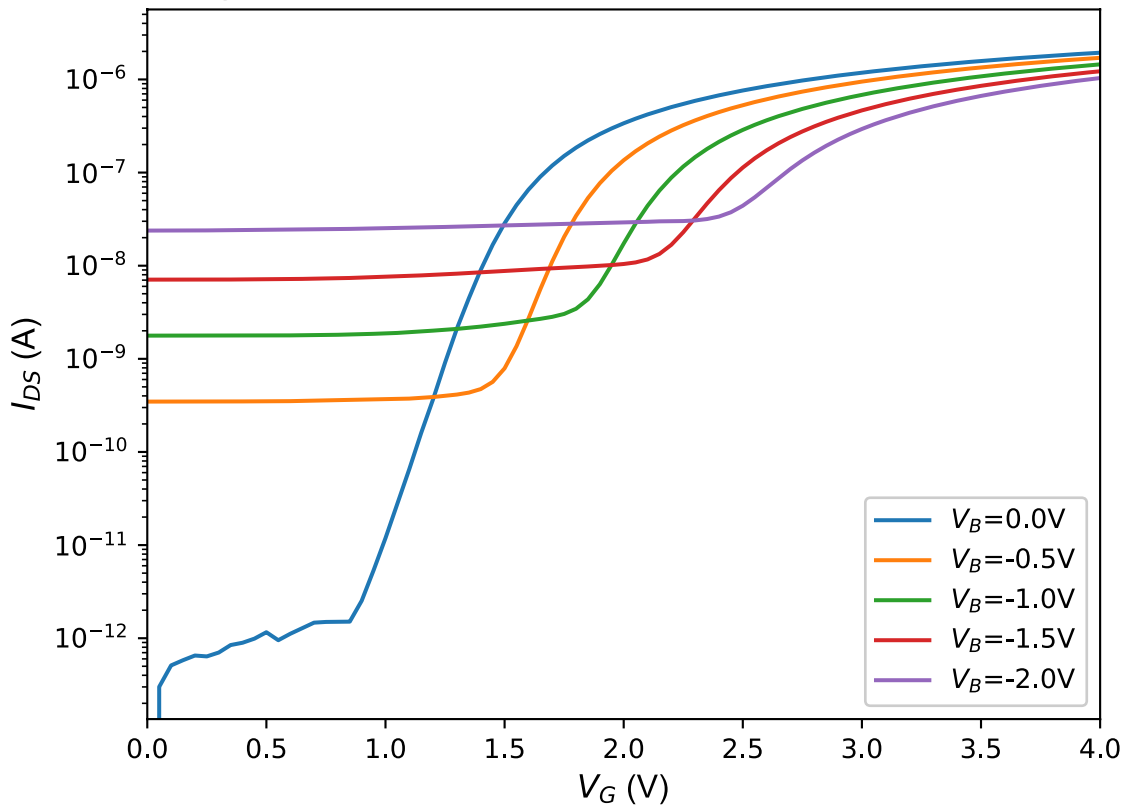
I_{DS} - V_{DS} characteristics for L=100 μ m W=100 μ m nMOS transistor



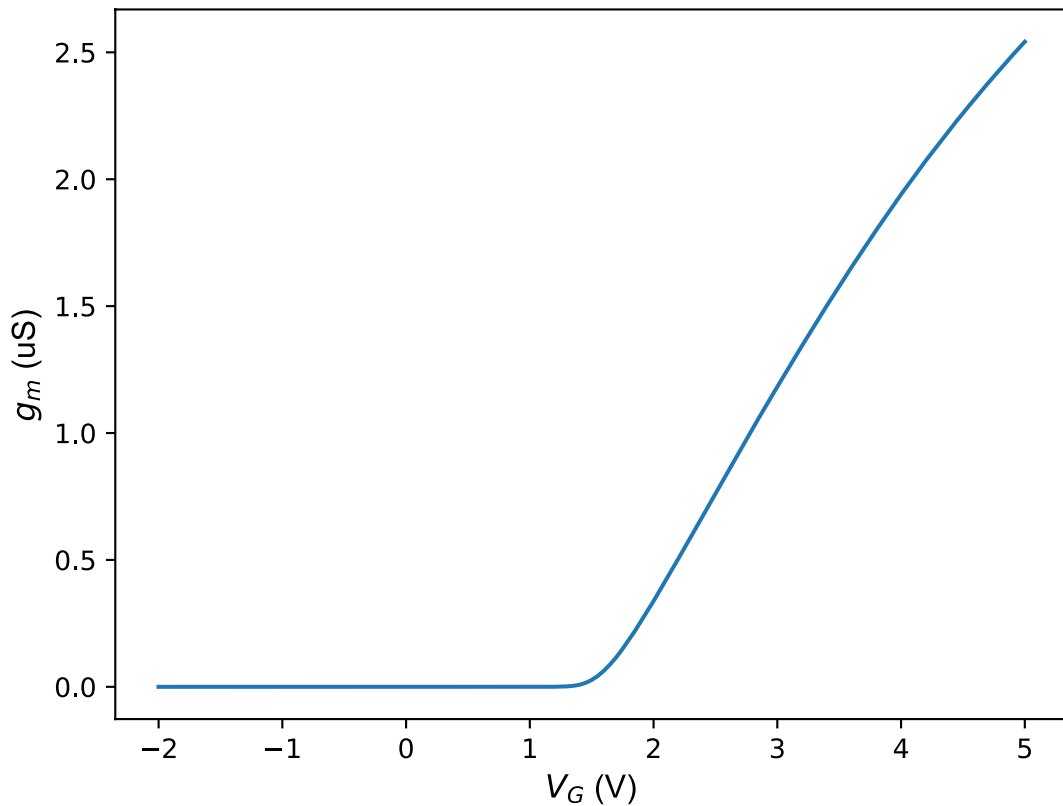
$I_{DS}-V_G$ for L=100um W=100um nMOS transistor



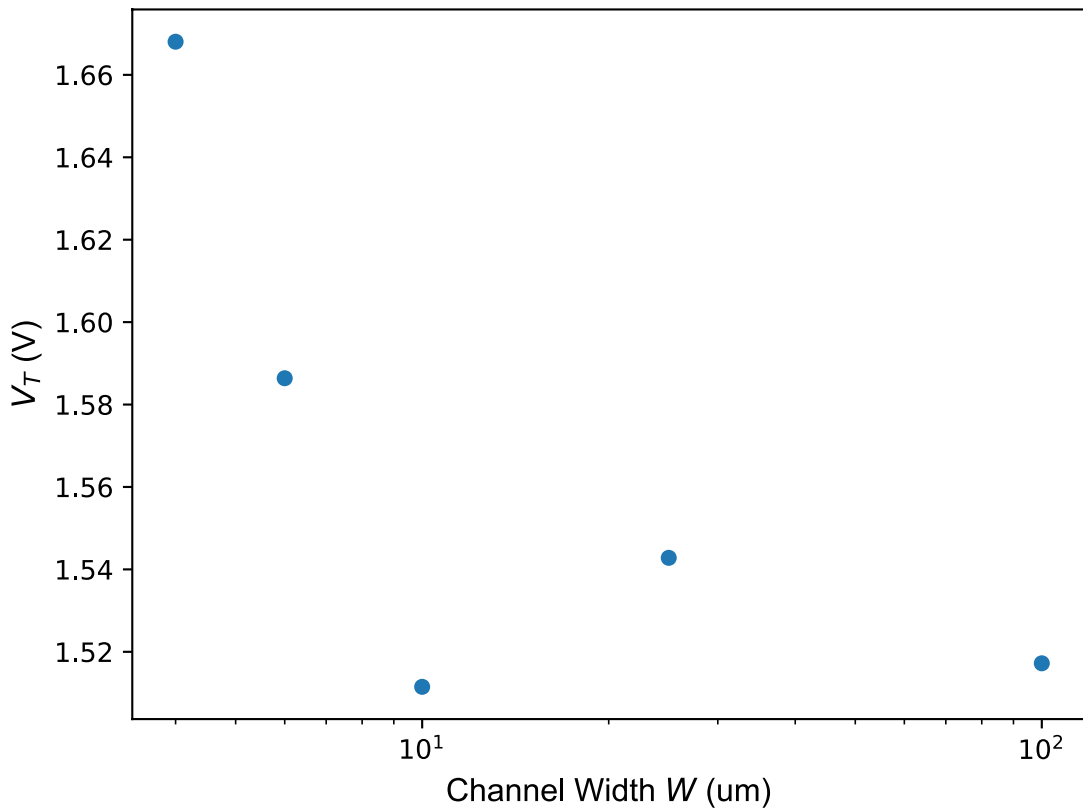
Body bias effect for L=100um W=100um nMOS transistor



Transconductance for L=100um W=100um nMOS transistor



Threshold voltage (V_T) at different channel widths



Threshold voltage (V_T) at different channel lengths

